

## Automotive 8K x 8 SRAM

### Features

- 8192 x 8 bit static CMOS RAM
- 70 ns Access Time
- Common data inputs and outputs
- Three-state outputs
- Typ. operating supply current: 30 mA
- TTL/CMOS-compatible
- Automatic reduction of power dissipation in long Read or Write cycles
- Power supply voltage 5 V
- Operating temperature ranges -40 to 125 °C
- Quality assessment according to CECC 90000, CECC 90100 and CECC 90111
- ESD protection > 2000 V (MIL STD 883C M3015.7)
- Latch-up immunity > 100 mA
- Packages: SOP28 (300 mil)  
SOP28 (330 mil)

### Description

The U6264ASA07 is a static RAM manufactured using a CMOS process technology with the following operating modes:

- Read            - Standby
- Write          - Data Retention

The memory array is based on a 6-transistor cell.

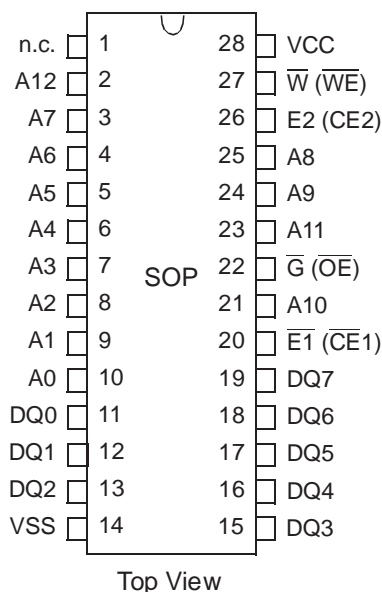
The circuit is activated by the rising edge of E2 (at  $\overline{E1} = L$ ), or the falling edge of  $\overline{E1}$  (at E2 = H). The address and control inputs open simultaneously. According to the information of  $\overline{W}$  and  $\overline{G}$ , the data inputs, or outputs, are active. During the active state ( $\overline{E1} = L$  and E2 = H), each address change leads to a new Read or Write cycle. In a Read cycle, the data outputs are activated by the falling edge of  $\overline{G}$ , afterwards the data word read will be available at the outputs DQ0 - DQ7. After the address

change, the data outputs go High-Z until the new read information is available. The full CMOS data outputs have no preferred state. If the memory is driven by CMOS levels in the active state, and if there is no change of the address, data input and control signals  $\overline{W}$  or  $\overline{G}$ , the operating current (at  $I_O = 0$  mA) drops to the value of the operating current in the Standby mode. The Read cycle is finished by the falling edge of E2 or  $\overline{W}$ , or by the rising edge of  $\overline{E1}$ , respectively.

Data retention is guaranteed down to 2 V. With the exception of E2, all inputs consist of NOR gates, so that no pull-up/pull-down resistors are required. This gate circuit allows to achieve low power standby requirements by activation with TTL-levels too.

If the circuit is inactivated by E2 = L, the standby current (TTL) drops to 150  $\mu$ A typ.

### Pin Configuration

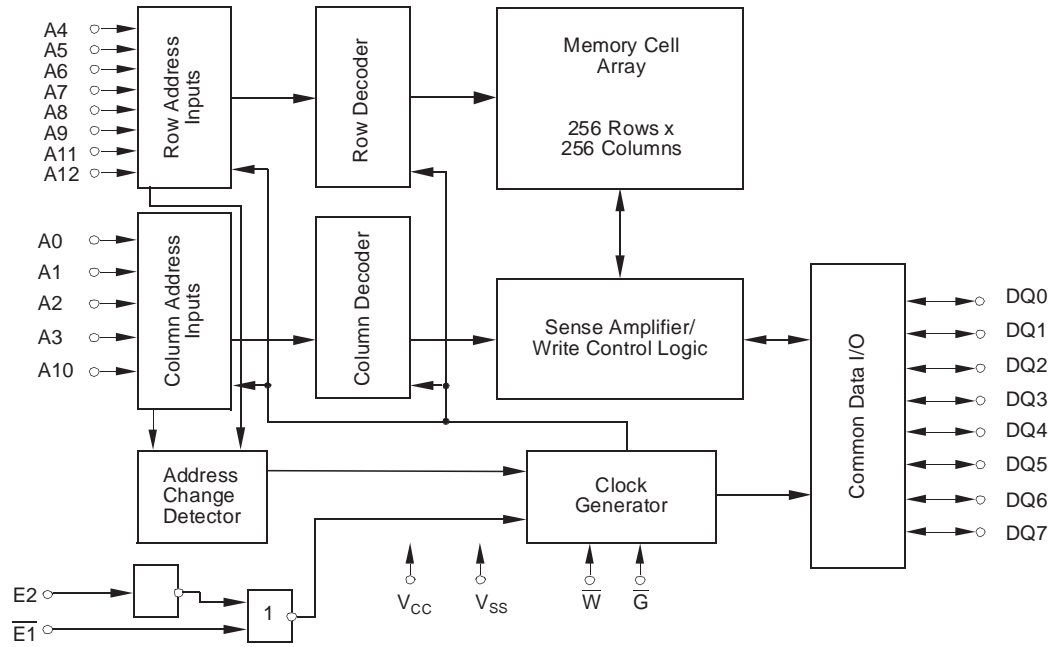


### Pin Description

Signal Name	Signal Description
A0 - A12	Address Inputs
DQ0 - DQ7	Data In/Outputs
$\overline{E1}$	Chip Enable 1
E2	Chip Enable 2
$\overline{G}$	Output Enable
$\overline{W}$	Read/Write Enable
VCC	Power Supply Voltage
VSS	Ground
n.c.	not connected

# U6264ASA07

## Block Diagram



## Truth Table

Operating Mode	$\overline{E1}$	E2	$\overline{W}$	$\overline{G}$	DQ0 - DQ7
Standby/not selected	*	L	*	*	High-Z
	H	*	*	*	High-Z
Internal Read	L	H	H	H	High-Z
Read	L	H	H	L	Data Outputs, Low-Z
Write	L	H	L	*	Data Inputs, High-Z

\* H or L

## Characteristics

All voltages are referenced to  $V_{SS} = 0$  V (ground).

All characteristics are valid in the power supply voltage range and in the operating temperature range specified.

Dynamic measurements are based on a rise and fall time of  $\leq 5$  ns, measured between 10 % and 90 % of  $V_I$ , as well as input levels of  $V_{IL} = 0$  V and  $V_{IH} = 3$  V. The timing reference level of all input and output signals is 1.5 V, with the exception of the  $t_{dis}$ -times, in which cases transition is measured  $\pm 200$  mV from steady-state voltage.

Maximum Ratings	Symbol	Min.	Max.	Unit
Power Supply Voltage	$V_{CC}$	-0.3	7	V
Input Voltage	$V_I$	-0.3	$V_{CC} + 0.5$	V
Output Voltage	$V_O$	-0.3	$V_{CC} + 0.5$	V
Power Dissipation	$P_D$		1	W
Operating Temperature	$T_a$	-40	125	$^{\circ}$ C
Storage Temperature	$T_{stg}$	-65	150	$^{\circ}$ C

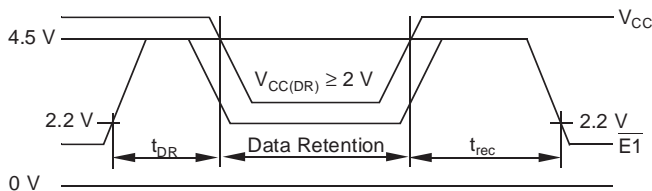
Recommended Operating Conditions	Symbol	Conditions	Min.	Max.	Unit
Power Supply Voltage	$V_{CC}$		4.5	5.5	V
Data Retention Voltage	$V_{CC(DR)}$		2.0	-	V
Input Low Voltage*	$V_{IL}$		-0.3	0.8	V
Input High Voltage	$V_{IH}$		2.2	$V_{CC}+0.3$	V

\* -2 V at Pulse Width 10 ns

Electrical Characteristics	Symbol	Conditions	Min.	Max.	Unit
Supply Current - Operating Mode	$I_{CC(OP)}$	$V_{CC} = 5.5\text{ V}$ $V_{IL} = 0.8\text{ V}$ $V_{IH} = 2.2\text{ V}$ $t_{cW} = 70\text{ ns}$		55	mA
Supply Current - Standby Mode (TTL level)	$I_{CC(SB)1}$	$V_{CC} = 5.5\text{ V}$ $V_{E1} = V_{E2} = 2.2\text{ V}$ or $V_{E2} = 0.8\text{ V}$		3	mA
Output High Voltage TTL compatible CMOS compatible	$V_{OH}$ $V_{OH}$	$V_{CC} = 4.5\text{ V}$ $I_{OH} = -1.0\text{ mA}$	2.4 $0.85 \cdot V_{CC}$	- -	V V
Output Low Voltage	$V_{OL}$	$V_{CC} = 4.5\text{ V}$ $I_{OL} = 3.2\text{ mA}$	-	0.4	V
Output High Current	$I_{OH}$	$V_{CC} = 4.5\text{ V}$ $V_{OH} = 2.4\text{ V}$	-	-1	mA
Output Low Current	$I_{OL}$	$V_{CC} = 4.5\text{ V}$ $V_{OL} = 0.4\text{ V}$	3.2	-	mA
Supply Current - Standby Mode (CMOS level)	$I_{CC(SB)}$	$V_{CC} = 5.5\text{ V}$ $V_{E1} = V_{E2} = V_{CC} - 0.2\text{ V}$ or $V_{E2} = 0.2\text{ V}$		30	$\mu\text{A}$
Supply Current - Data Retention Mode	$I_{CC(DR)}$	$V_{CC(DR)} = 3\text{ V}$ $V_{E1} = V_{E2} = V_{CC(DR)} - 0.2\text{ V}$ or $V_{E2} = 0.2\text{ V}$		10	$\mu\text{A}$
Input High Leakage Current	$I_{IH}$	$V_{CC} = 5.5\text{ V}$ $V_{IH} = 5.5\text{ V}$	-	2	$\mu\text{A}$
Input Low Leakage Current	$I_{IL}$	$V_{CC} = 5.5\text{ V}$ $V_{IL} = 0\text{ V}$	-2	-	$\mu\text{A}$
Output Leakage Current High at Three-State Outputs	$I_{OHZ}$	$V_{CC} = 5.5\text{ V}$ $V_{OH} = 5.5\text{ V}$	-	2	$\mu\text{A}$
Low at Three-State Outputs	$I_{OLZ}$	$V_{CC} = 5.5\text{ V}$ $V_{OL} = 0\text{ V}$	-2	-	$\mu\text{A}$

Switching Characteristics	Symbol		Min.	Max.	Unit
	Alt.	IEC			
Time to Output in Low-Z	$t_{LZ}$	$t_{t(QX)}$	5	10	ns
Cycle Time					
Write Cycle Time	$t_{WC}$	$t_{cW}$	70	-	ns
Read Cycle Time	$t_{RC}$	$t_{cR}$	70	-	ns
Access Time					
$\overline{E1}$ LOW or E2 HIGH to Data Valid	$t_{ACE}$	$t_{a(E)}$	-	70	ns
$\overline{G}$ LOW to Data Valid	$t_{OE}$	$t_{a(G)}$	-	40	ns
Address to Data Valid	$t_{AA}$	$t_{a(A)}$	-	70	ns
Pulse Widths					
Write Pulse Width	$t_{WP}$	$t_{w(W)}$	50	-	ns
Chip Enable to End of Write	$t_{CW}$	$t_{w(E)}$	65	-	ns
Setup Times					
Address Setup Time	$t_{AS}$	$t_{su(A)}$	0	-	ns
Chip Enable to End of Write	$t_{CW}$	$t_{su(E)}$	65	-	ns
Write Pulse Width	$t_{WP}$	$t_{su(W)}$	50	-	ns
Data Setup Time	$t_{DS}$	$t_{su(D)}$	35	-	ns
Data Hold Time	$t_{DH}$	$t_{h(D)}$	0	-	ns
Address Hold from End of Write	$t_{AH}$	$t_{h(A)}$	0	-	ns
Output Hold Time from Address Change	$t_{OH}$	$t_{v(A)}$	5	-	ns
$\overline{E1}$ HIGH or E2 LOW to Output in High-Z	$t_{HZCE}$	$t_{dis(E)}$	0	25	ns
$\overline{W}$ LOW to Output in High-Z	$t_{HZWE}$	$t_{dis(W)}$	0	30	ns
$\overline{G}$ HIGH to Output in High-Z	$t_{HZOE}$	$t_{dis(G)}$	0	25	ns

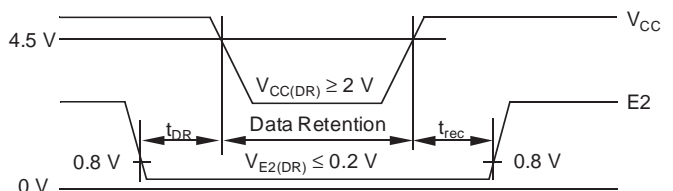
### Data Retention Mode $\overline{E1}$ -Controlled



$$V_{E2(DR)} \geq V_{CC(DR)} - 0.2 \text{ V or } V_{E2(DR)} \leq 0.2 \text{ V}$$

$$V_{CC(DR)} - 0.2 \text{ V} \leq V_{\overline{E1}(DR)} \leq V_{CC(DR)} + 0.3 \text{ V}$$

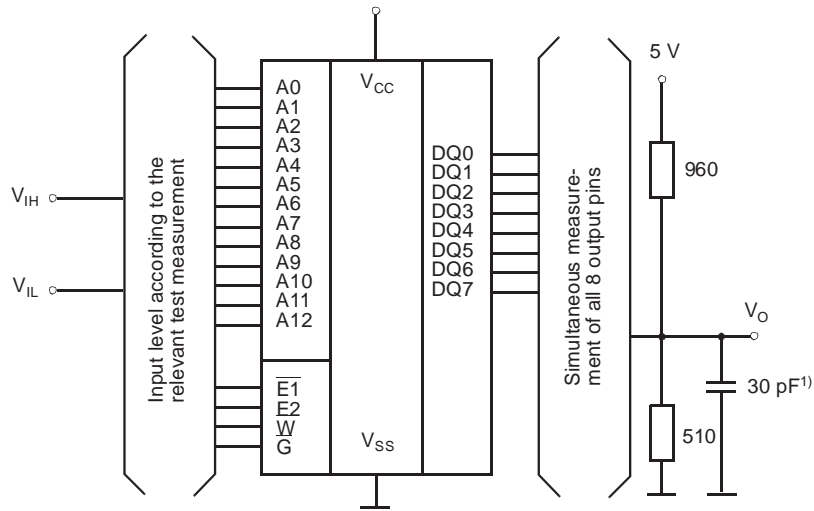
### Data Retention Mode E2-Controlled



Chip Deselect to Data Retention Time  
Operating Recovery Time

$t_{DR}$ : min 0 ns  
 $t_{rec}$ : min  $t_{cR}$

## Test Configuration for Functional Check (for TTL output levels)



1) In measurement of  $t_{dis(E)}$ ,  $t_{dis(W)}$ ,  $t_{dis(G)}$  the capacitance is 5 pF.

Capacitance	Conditions	Symbol	Min.	Max.	Unit
Input Capacitance	$V_{CC} = 5.0\text{ V}$ $V_I = V_{SS}$	$C_I$		8	pF
Output Capacitance	$f = 1\text{ MHz}$ $T_a = 25\text{ °C}$	$C_O$		10	pF

All pins not under test must be connected with ground by capacitors.

### IC Code Numbers

Example

U6264A S A 07

Type

Package

S1 = SOP28 (300 mil)

S = SOP28 (330 mil)

Operating Temperature Range

A = -40 to 125 °C

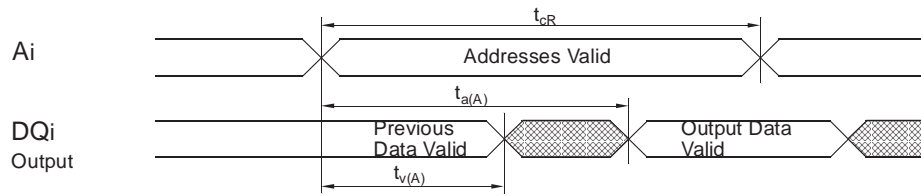
Internal Code

Access Time

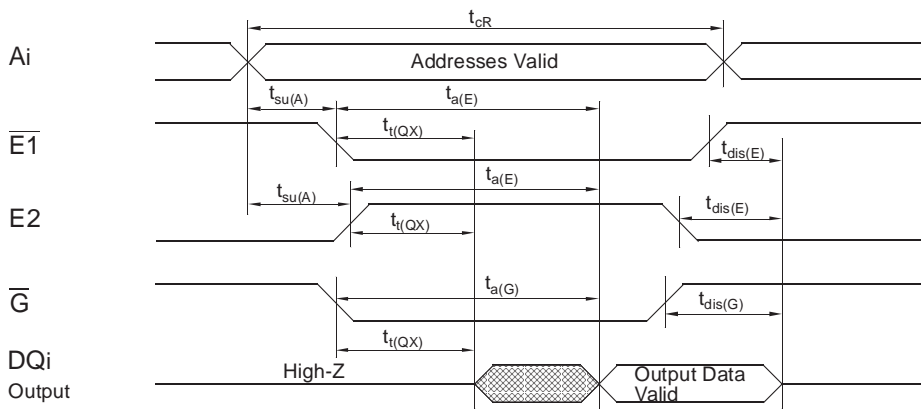
07 = 70 ns

The date of manufacture is given by the last 4 digits of the mark, the first 2 digits indicating the year, and the last 2 digits the calendar week.

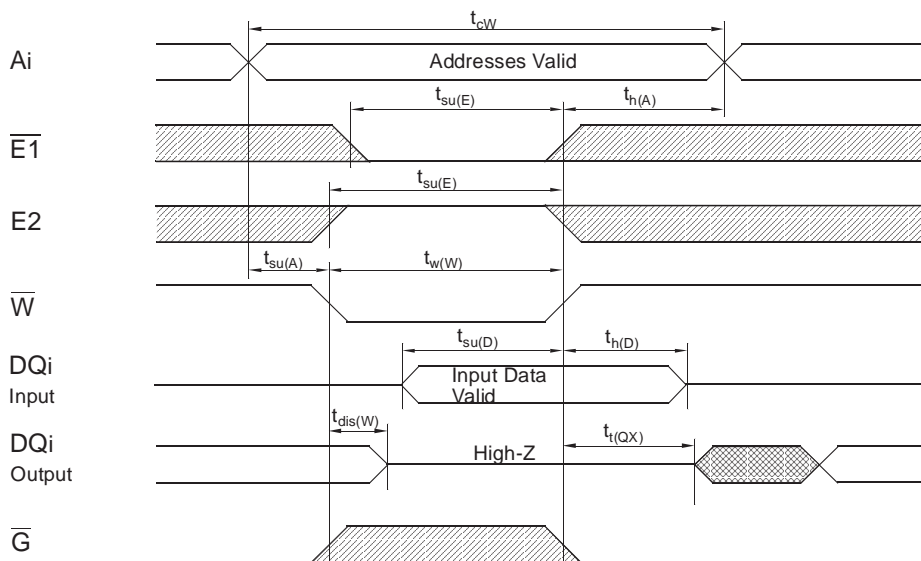
## Read Cycle 1 (during Read cycle: $\overline{E1} = \overline{G} = V_{IL}$ , $E2 = \overline{W} = V_{IH}$ )



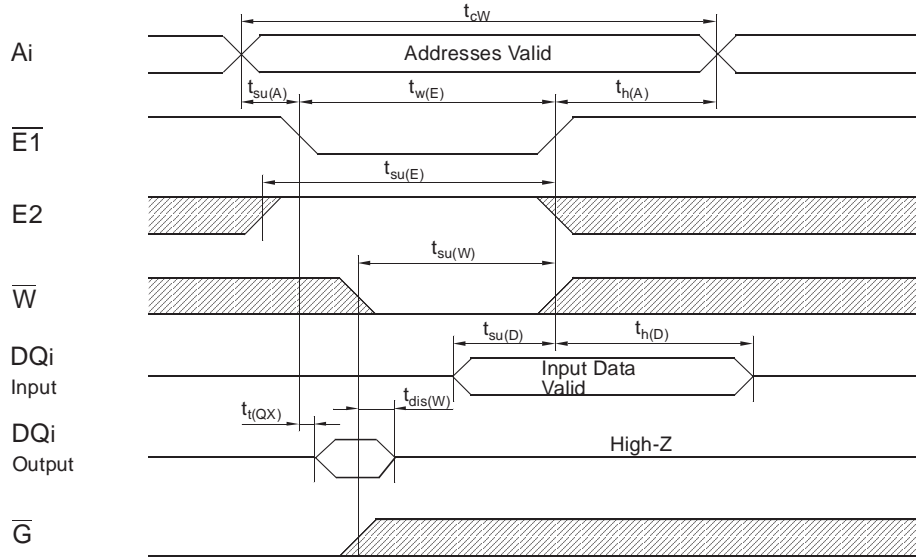
## Read Cycle 2 (during Read cycle: $\overline{W} = V_{IH}$ )



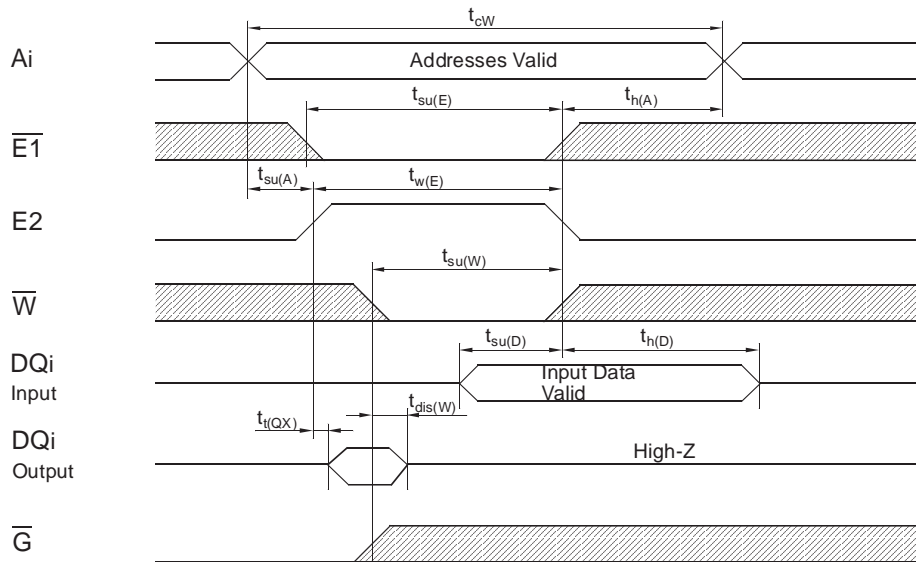
## Write Cycle 1 ( $\overline{W}$ -controlled)



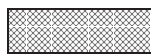
Write Cycle 2 ( $\overline{E1}$ -controlled)



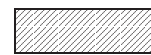
Write Cycle 3 (E2-controlled)



undefined



L- or H-level





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## **Memory Products 1998**

### **Automotive 8K x 8 SRAM U6264ASA07**

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